

ZXM62N03E6

30V N-CHANNEL ENHANCEMENT MODE MOSFET

SUMMARY

$V_{(BR)DSS}=30V$; $R_{DS(ON)}=0.11\Omega$; $I_D=3.2A$

DESCRIPTION

This new generation of high density MOSFETs from Zetex utilise a unique structure that combines the benefits of low on-resistance with fast switching speed. This makes them ideal for high efficiency, low voltage, power management applications.

FEATURES

- Low on-resistance
- Fast switching speed
- Low threshold
- Low gate drive
- SOT23-6 package

APPLICATIONS

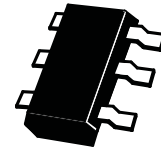
- DC - DC converters
- Power management functions
- Disconnect switches
- Motor control

ORDERING INFORMATION

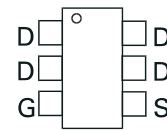
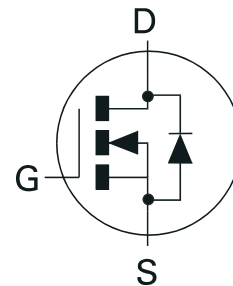
DEVICE	REEL SIZE (inches)	TAPE WIDTH (mm)	QUANTITY PER REEL
ZXM62N03E6TA	7	8mm embossed	3000 units
ZXM62N03E6TC	13	8mm embossed	10000 units

DEVICE MARKING

- 2N03



SOT23-6



Top View

ZXM62N03E6

ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	LIMIT	UNIT
Drain-Source Voltage	V_{DSS}	30	V
Gate Source Voltage	V_{GS}	± 20	V
Continuous Drain Current ($V_{GS}=10V$; $T_A=25^\circ C$)(b) ($V_{GS}=10V$; $T_A=70^\circ C$)(b)	I_D	3.2 2.6	A
Pulsed Drain Current (c)	I_{DM}	18	A
Continuous Source Current (Body Diode) (b)	I_S	2.1	A
Pulsed Source Current (Body Diode)	I_{SM}	18	A
Power Dissipation at $T_A=25^\circ C$ (a) Linear Derating Factor	P_D	1.1 8.8	W mW/ $^\circ C$
Power Dissipation at $T_A=25^\circ C$ (b) Linear Derating Factor	P_D	1.7 13.6	W mW/ $^\circ C$
Operating and Storage Temperature Range	T_j ; T_{stg}	-55 to +150	$^\circ C$

THERMAL RESISTANCE

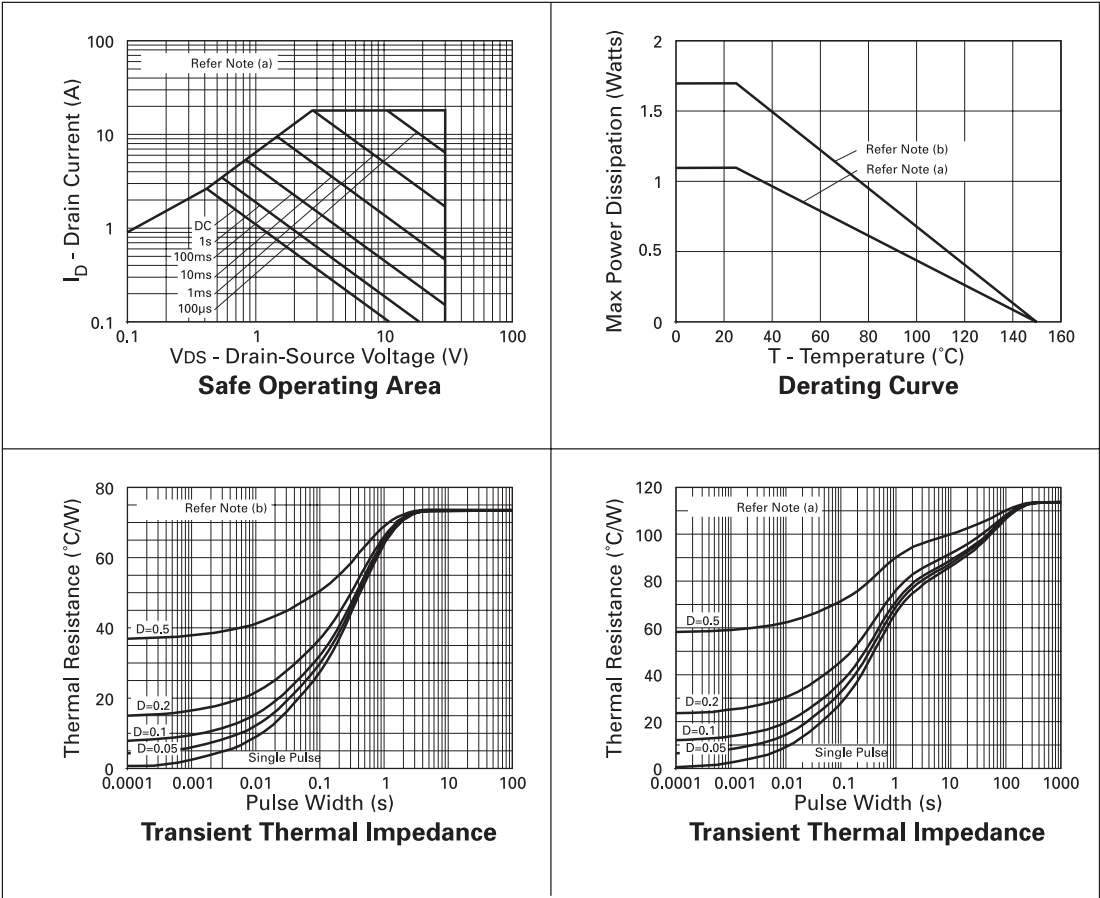
PARAMETER	SYMBOL	VALUE	UNIT
Junction to Ambient (a)	$R_{\theta JA}$	113	$^\circ C/W$
Junction to Ambient (b)	$R_{\theta JA}$	73	$^\circ C/W$

NOTES:

- (a) For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions
- (b) For a device surface mounted on FR4 PCB measured at $t \leq 5$ secs.
- (c) Repetitive rating - pulse width limited by maximum junction temperature. Refer to Transient Thermal Impedance graph.

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CHARACTERISTICS



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ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}\text{C}$ unless otherwise stated)

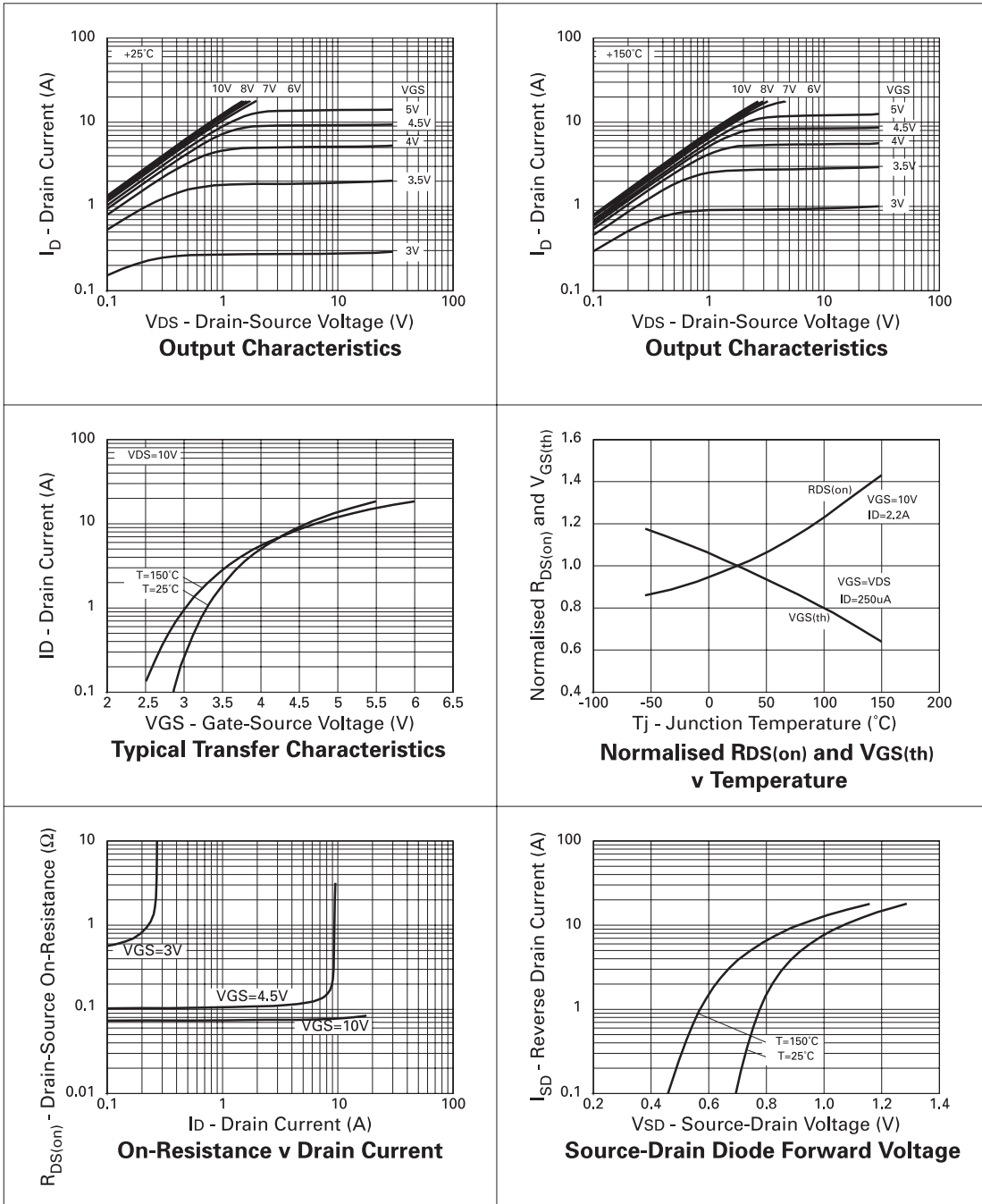
PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS.
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	30			V	$I_D=250\mu\text{A}, V_{GS}=0\text{V}$
Zero Gate Voltage Drain Current	I_{DSS}			1	μA	$V_{DS}=30\text{V}, V_{GS}=0\text{V}$
Gate-Body Leakage	I_{GSS}			100	nA	$V_{GS}=(\quad)20\text{V}, V_{DS}=0\text{V}$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1.0			V	$I_D=250\mu\text{A}, V_{DS}=V_{GS}$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$			0.11 0.15	Ω Ω	$V_{GS}=10\text{V}, I_D=2.2\text{A}$ $V_{GS}=4.5\text{V}, I_D=1.1\text{A}$
Forward Transconductance	g_{fs}	1.1			S	$V_{DS}=10\text{V}, I_D=1.1\text{A}$
DYNAMIC (3)						
Input Capacitance	C_{iss}		380		pF	$V_{DS}=25\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}$
Output Capacitance	C_{oss}		90		pF	
Reverse Transfer Capacitance	C_{rss}		30		pF	
SWITCHING(2) (3)						
Turn-On Delay Time	$t_{d(on)}$		2.9		ns	$V_{DD}=15\text{V}, I_D=2.2\text{A}$ $R_G=6.0\Omega, R_D=6.7\Omega$ (refer to test circuit)
Rise Time	t_r		5.6		ns	
Turn-Off Delay Time	$t_{d(off)}$		11.7		ns	
Fall Time	t_f		6.4		ns	
Total Gate Charge	Q_g			9.6	nC	$V_{DS}=24\text{V}, V_{GS}=10\text{V},$ $I_D=2.2\text{A}$ (refer to test circuit)
Gate-Source Charge	Q_{gs}			1.7	nC	
Gate Drain Charge	Q_{gd}			2.8	nC	
SOURCE-DRAIN DIODE						
Diode Forward Voltage (1)	V_{SD}			0.95	V	$T_j=25^{\circ}\text{C}, I_S=2.2\text{A},$ $V_{GS}=0\text{V}$
Reverse Recovery Time (3)	t_{rr}		18.8		ns	$T_j=25^{\circ}\text{C}, I_F=2.2\text{A},$ $di/dt=100\text{A}/\mu\text{s}$
Reverse Recovery Charge (3)	Q_{rr}		11.4		nC	

(1) Measured under pulsed conditions. Width=300 μs . Duty cycle @2% .

(2) Switching characteristics are independent of operating junction temperature.

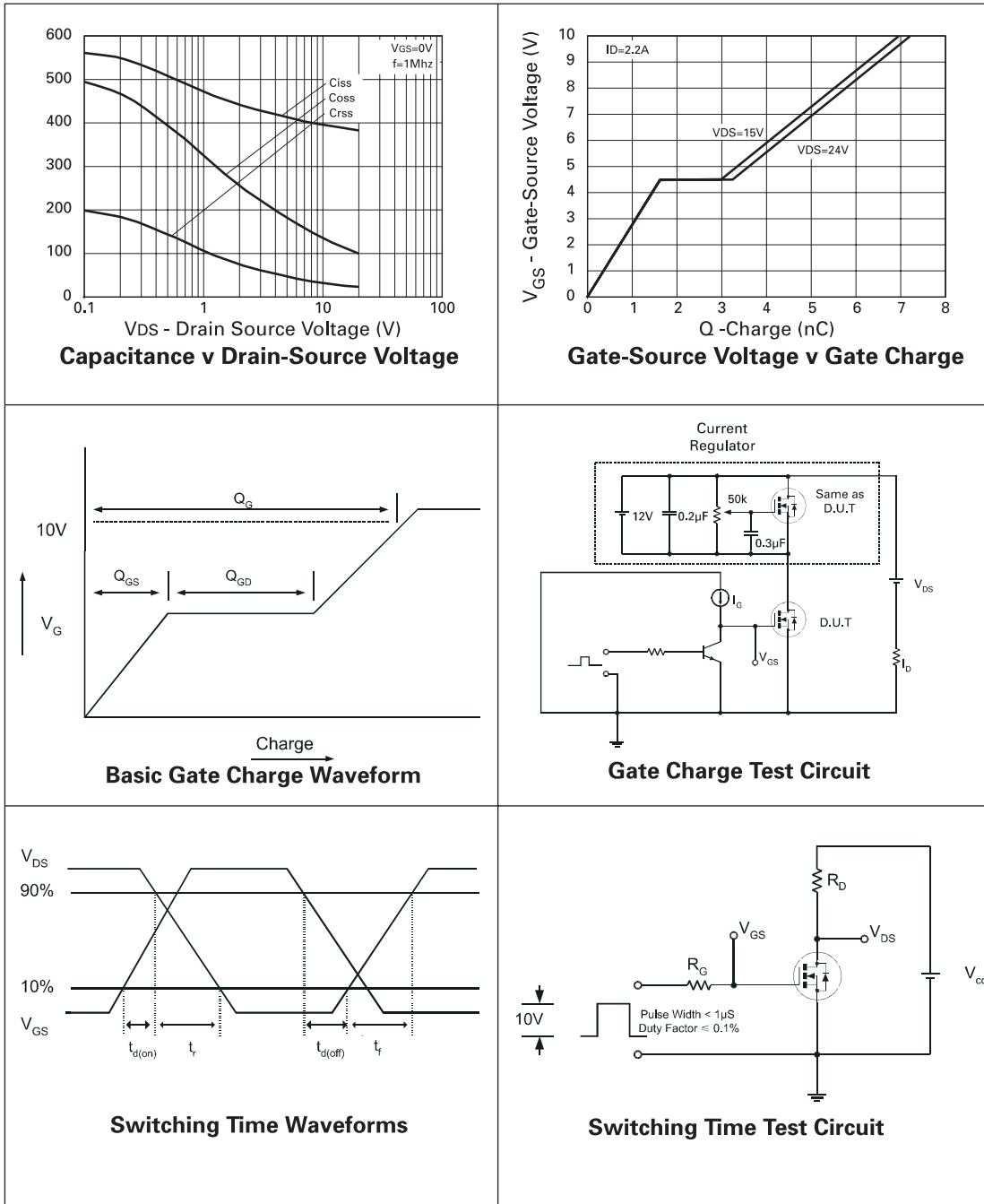
(3) For design aid only, not subject to production testing.

TYPICAL CHARACTERISTICS



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TYPICAL CHARACTERISTICS



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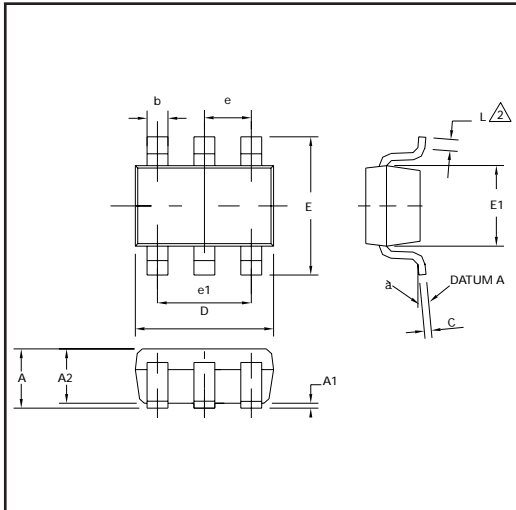
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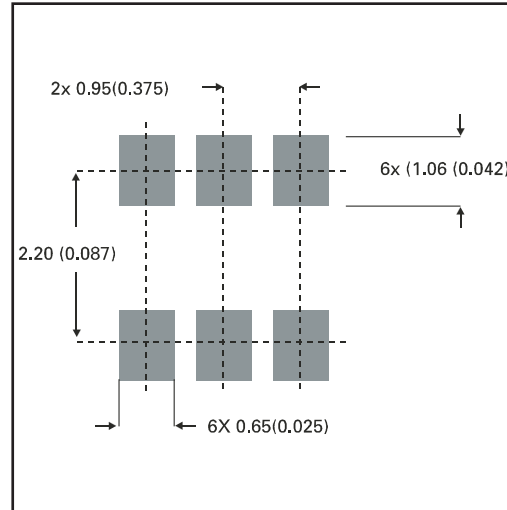


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PACKAGE DIMENSIONS



PAD LAYOUT DETAILS



DIM	Millimeters		Inches	
	Min	Max	Min	Max
A	0.90	1.45	0.35	0.057
A1	0.00	0.15	0	0.006
A2	0.90	1.30	0.035	0.051
b	0.35	0.50	0.014	0.019
C	0.09	0.20	0.0035	0.008
D	2.80	3.00	0.110	0.118
E	2.60	3.00	0.102	0.118
E1	1.50	1.75	0.059	0.069

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